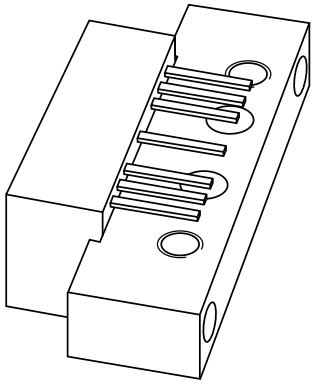
DATA SHEET



BGD804

860 MHz, 20 dB gain power doubler amplifier

Product specification
Supersedes data of 1999 Mar 26

2001 Nov 01

860 MHz, 20 dB gain power doubler amplifier

BGD804

FEATURES

- Excellent linearity
- Extremely low noise
- Silicon nitride passivation
- Rugged construction
- Gold metallization ensures excellent reliability.

APPLICATIONS

CATV systems in the 40 to 860 MHz frequency range.

DESCRIPTION

Hybrid amplifier module in a SOT115J package operating at a voltage supply of 24 V (DC).

PINNING - SOT115J

PIN	DESCRIPTION
1	input
2	common
3	common
5	$+V_B$
7	common
8	common
9	output

PIN CONFIGURATION

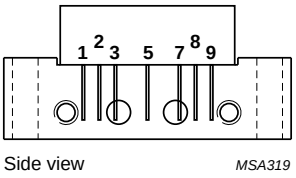


Fig.1 Simplified outline.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
G_p	power gain	f = 50 MHz	19.5	20.5	dB
		f = 860 MHz	20	–	dB
I_{tot}	total current consumption (DC)	V_B = 24 V	–	410	mA

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	MIN.	MAX.	UNIT
V_i	RF input voltage	–	65	dBmV
T_{stg}	storage temperature	–40	+100	°C
T_{mb}	operating mounting base temperature	–20	+100	°C
V_B	supply voltage	–	25	V

CHARACTERISTICS

Table 1 Bandwidth 40 to 860 MHz; V_B = 24 V; T_{case} = 35 °C; $Z_S = Z_L$ = 75 Ω

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
G_p	power gain	f = 50 MHz	19.5	20	20.5	dB
		f = 860 MHz	20	21	–	dB
SL	slope cable equivalent	f = 40 to 860 MHz	0.2	1.1	2	dB
FL	flatness of frequency response	f = 40 to 860 MHz	–	±0.2	±0.5	dB
S_{11}	input return losses	f = 40 to 80 MHz	20	28	–	dB
		f = 80 to 160 MHz	18.5	23	–	dB
		f = 160 to 320 MHz	17	20	–	dB
		f = 320 to 640 MHz	15.5	20	–	dB
		f = 640 to 860 MHz	14	20	–	dB
S_{22}	output return losses	f = 40 to 80 MHz	20	28.5	–	dB
		f = 80 to 160 MHz	18.5	28	–	dB
		f = 160 to 320 MHz	17	24	–	dB
		f = 320 to 640 MHz	15.5	19	–	dB
		f = 640 to 860 MHz	14	19	–	dB
S_{21}	phase response	f = 50 MHz	–45	–	+45	deg
CTB	composite triple beat	49 channels flat; V_o = 47 dBmV; measured at 859.25 MHz	–	–64	–61	dB
X_{mod}	cross modulation	49 channels flat; V_o = 47 dBmV; measured at 55.25 MHz	–	–65.5	–62	dB
CSO	composite second order distortion	49 channels flat; V_o = 47 dBmV; measured at 860.5 MHz	–	–63	–58	dB
d_2	second order distortion	note 1	–	–73	–67	dB
V_o	output voltage	d_{im} = –60 dB; note 2	+60	–61.5	–	dBmV
F	noise figure	f = 50 MHz	–	4.5	5	dB
		f = 550 MHz	–	–	6	dB
		f = 650 MHz	–	–	6	dB
		f = 750 MHz	–	–	6.5	dB
		f = 860 MHz	–	6.5	7.5	dB
I_{tot}	total current consumption (DC)	note 3	–	395	410	mA

Notes

1. f_p = 55.25 MHz; V_p = 44 dBmV;
   f_q = 805.25 MHz; V_q = 44 dBmV;
   measured at $f_p + f_q$ = 860.5 MHz.
2. Measured according to DIN45004B;
   f_p = 851.25 MHz; $V_p = V_o$;
   f_q = 858.25 MHz; $V_q = V_o$ –6 dB;
   f_r = 860.25 MHz; $V_r = V_o$ –6 dB;
   measured at $f_p + f_q - f_r$ = 849.25 MHz.
3. The module normally operates at V_B = 24 V, but is able to withstand supply transients up to 30 V.

Table 2 Bandwidth 40 to 860 MHz; V_B = 24 V; T_{case} = 35 °C; $Z_S = Z_L$ = 75 Ω

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
G_p	power gain	f = 50 MHz	19.5	20	20.5	dB
		f = 860 MHz	20	21	–	dB
SL	slope cable equivalent	f = 40 to 860 MHz	0.2	1.1	2	dB
FL	flatness of frequency response	f = 40 to 860 MHz	–	±0.2	±0.5	dB
S_{11}	input return losses	f = 40 to 80 MHz	20	28	–	dB
		f = 80 to 160 MHz	18.5	23	–	dB
		f = 160 to 320 MHz	17	20	–	dB
		f = 320 to 640 MHz	15.5	20	–	dB
		f = 640 to 860 MHz	14	20	–	dB
S_{22}	output return losses	f = 40 to 80 MHz	20	28.5	–	dB
		f = 80 to 160 MHz	18.5	28	–	dB
		f = 160 to 320 MHz	17	24	–	dB
		f = 320 to 640 MHz	15.5	19	–	dB
		f = 640 to 860 MHz	14	19	–	dB
S_{21}	phase response	f = 50 MHz	−45	–	+45	deg
CTB	composite triple beat	129 channels flat; V_o = 44 dBmV; measured at 859.25 MHz	–	−54	−53	dB
X_{mod}	cross modulation	129 channels flat; V_o = 44 dBmV; measured at 55.25 MHz	–	−62	−61	dB
CSO	composite second order distortion	129 channels flat; V_o = 44 dBmV; measured at 860.5 MHz	–	−60.5	−54	dB
d_2	second order distortion	note 1	–	−73	−67	dB
V_o	output voltage	d_{im} = −60 dB; note 2	+60	−61.5	–	dBmV
F	noise figure	see Table 1	–	–	–	dB
I_{tot}	total current consumption (DC)	note 3	–	395	410	mA

Notes

1. f_p = 55.25 MHz; V_p = 44 dBmV;
   f_q = 805.25 MHz; V_q = 44 dBmV;
   measured at $f_p + f_q$ = 860.5 MHz.
2. Measured according to DIN45004B;
   f_p = 851.25 MHz; $V_p = V_o$;
   f_q = 858.25 MHz; $V_q = V_o$ −6 dB;
   f_r = 860.25 MHz; $V_r = V_o$ −6 dB;
   measured at $f_p + f_q - f_r$ = 849.25 MHz.
3. The module normally operates at V_B = 24 V, but is able to withstand supply transients up to 30 V.

Table 3 Bandwidth 40 to 750 MHz; V_B = 24 V; T_{case} = 35 °C; $Z_S = Z_L$ = 75 Ω

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
G_p	power gain	f = 50 MHz	19.5	20	20.5	dB
		f = 750 MHz	20	20.8	–	dB
SL	slope cable equivalent	f = 40 to 750 MHz	0.2	–	2	dB
FL	flatness of frequency response	f = 40 to 750 MHz	–	–	±0.45	dB
S_{11}	input return losses	f = 40 to 80 MHz	20	28	–	dB
		f = 80 to 160 MHz	18.5	23	–	dB
		f = 160 to 320 MHz	17	20	–	dB
		f = 320 to 640 MHz	15.5	20	–	dB
		f = 640 to 750 MHz	14	20	–	dB
S_{22}	output return losses	f = 40 to 80 MHz	20	28.5	–	dB
		f = 80 to 160 MHz	18.5	28	–	dB
		f = 160 to 320 MHz	17	24	–	dB
		f = 320 to 640 MHz	15.5	19	–	dB
		f = 640 to 750 MHz	14	19	–	dB
S_{21}	phase response	f = 50 MHz	−45	–	+45	deg
CTB	composite triple beat	110 channels flat; V_o = 44 dBmV; measured at 745.25 MHz	–	−59	−57	dB
X_{mod}	cross modulation	110 channels flat; V_o = 44 dBmV; measured at 55.25 MHz	–	−64	−62	dB
CSO	composite second order distortion	110 channels flat; V_o = 44 dBmV; measured at 746.5 MHz	–	−62	−56	dB
d_2	second order distortion	note 1	–	–	−68	dB
V_o	output voltage	d_{im} = −60 dB; note 2	63	–	–	dBmV
F	noise figure	see Table 1	–	–	–	dB
I_{tot}	total current consumption (DC)	note 3	–	395	410	mA

Notes

1. f_p = 55.25 MHz; V_p = 44 dBmV;
   f_q = 691.25 MHz; V_q = 44 dBmV;
   measured at $f_p + f_q$ = 746.5 MHz.
2. Measured according to DIN45004B;
   f_p = 740.25 MHz; $V_p = V_o$;
   f_q = 747.25 MHz; $V_q = V_o$ −6 dB;
   f_r = 749.25 MHz; $V_r = V_o$ −6 dB;
   measured at $f_p + f_q - f_r$ = 738.25 MHz.
3. The module normally operates at V_B = 24 V, but is able to withstand supply transients up to 30 V.

Table 4 Bandwidth 40 to 650 MHz; V_B = 24 V; T_{case} = 35 °C; $Z_S = Z_L$ = 75 Ω

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
G_p	power gain	f = 50 MHz	19.5	20	20.5	dB
		f = 650 MHz	20	20.7	–	dB
SL	slope cable equivalent	f = 40 to 650 MHz	0.2	–	2	dB
FL	flatness of frequency response	f = 40 to 650 MHz	–	–	±0.35	dB
S_{11}	input return losses	f = 40 to 80 MHz	20	28	–	dB
		f = 80 to 160 MHz	18.5	23	–	dB
		f = 160 to 320 MHz	17	20	–	dB
		f = 320 to 650 MHz	15	20	–	dB
S_{22}	output return losses	f = 40 to 80 MHz	20	28.5	–	dB
		f = 80 to 160 MHz	18.5	28	–	dB
		f = 160 to 320 MHz	17	24	–	dB
		f = 320 to 650 MHz	15	19	–	dB
S_{21}	phase response	f = 50 MHz	−45	–	+45	deg
CTB	composite triple beat	94 channels flat; V_o = 44 dBmV; measured at 649.25 MHz	–	–	−60	dB
X_{mod}	cross modulation	94 channels flat; V_o = 44 dBmV; measured at 55.25 MHz	–	–	−62	dB
CSO	composite second order distortion	94 channels flat; V_o = 44 dBmV; measured at 650.5 MHz	–	–	−58	dB
d_2	second order distortion	note 1	–	–	−69	dB
V_o	output voltage	d_{im} = −60 dB; note 2	65	–	–	dBmV
F	noise figure	see Table 1	–	–	–	dB
I_{tot}	total current consumption (DC)	note 3	–	395	410	mA

Notes

1. f_p = 55.25 MHz; V_p = 44 dBmV;
   f_q = 595.25 MHz; V_q = 44 dBmV;
   measured at $f_p + f_q$ = 650.5 MHz.
2. Measured according to DIN45004B;
   f_p = 640.25 MHz; $V_p = V_o$;
   f_q = 647.25 MHz; $V_q = V_o$ −6 dB;
   f_r = 649.25 MHz; $V_r = V_o$ −6 dB;
   measured at $f_p + f_q - f_r$ = 638.25 MHz.
3. The module normally operates at V_B = 24 V, but is able to withstand supply transients up to 30 V.

Table 5 Bandwidth 40 to 550 MHz; V_B = 24 V; T_{case} = 35 °C; $Z_S = Z_L$ = 75 Ω

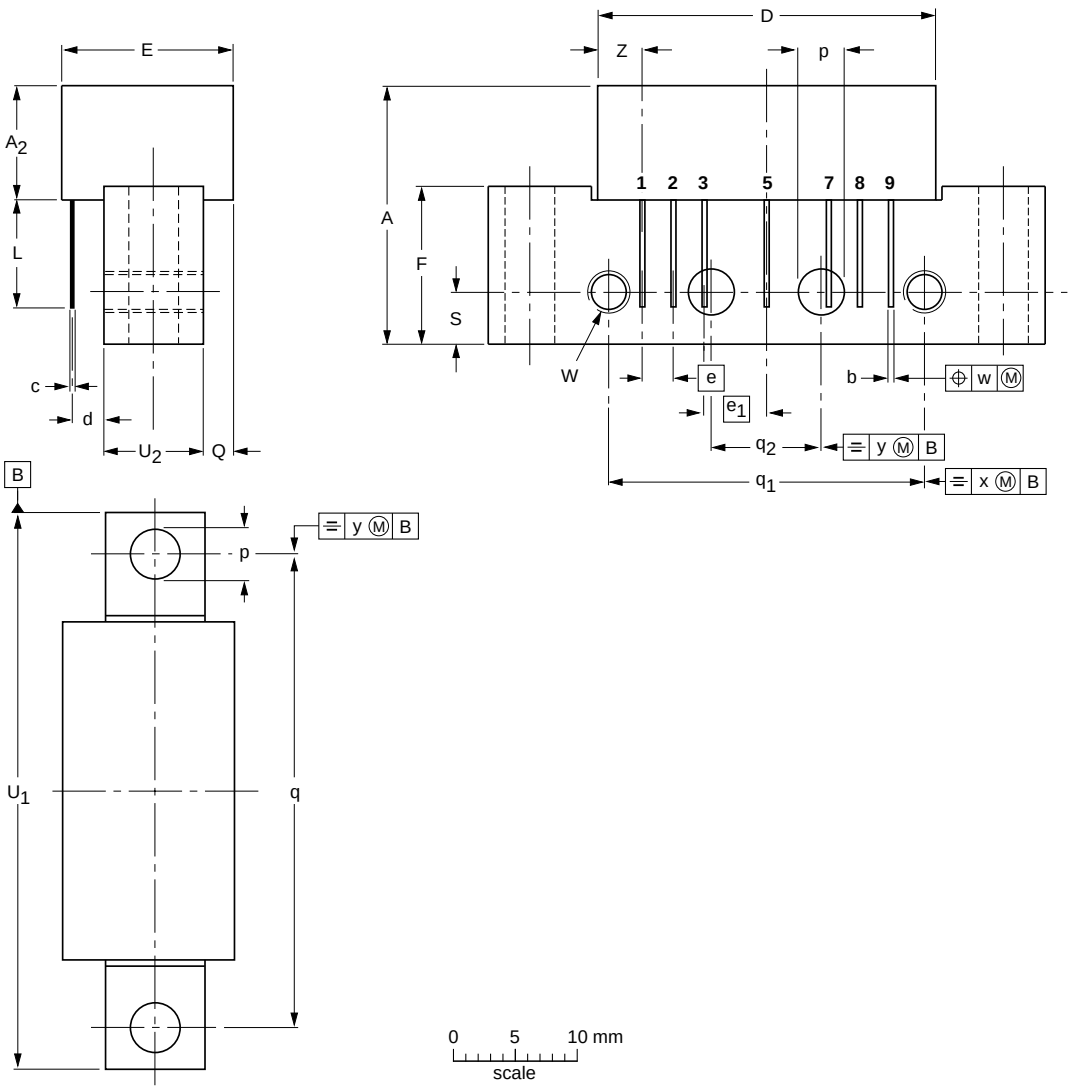
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
G_p	power gain	f = 50 MHz	19.5	20	20.5	dB
		f = 550 MHz	20	20.6	–	dB
SL	slope cable equivalent	f = 40 to 550 MHz	0.2	–	2	dB
FL	flatness of frequency response	f = 40 to 550 MHz	–	–	±0.35	dB
S_{11}	input return losses	f = 40 to 80 MHz	20	28	–	dB
		f = 80 to 160 MHz	18.5	23	–	dB
		f = 160 to 320 MHz	17	20	–	dB
		f = 320 to 550 MHz	16	20	–	dB
S_{22}	output return losses	f = 40 to 80 MHz	20	28.5	–	dB
		f = 80 to 160 MHz	18.5	28	–	dB
		f = 160 to 320 MHz	17	24	–	dB
		f = 320 to 550 MHz	16	19	–	dB
S_{21}	phase response	f = 50 MHz	−45	–	+45	deg
CTB	composite triple beat	77 channels flat; V_o = 44 dBmV; measured at 547.25 MHz	–	−66	−64	dB
X_{mod}	cross modulation	77 channels flat; V_o = 44 dBmV; measured at 55.25 MHz	–	−67	−64	dB
CSO	composite second order distortion	77 channels flat; V_o = 44 dBmV; measured at 548.5 MHz	–	−67	−62	dB
d_2	second order distortion	note 1	–	–	−72	dB
V_o	output voltage	d_{im} = −60 dB; note 2	66	–	–	dBmV
F	noise figure	see Table 1	–	–	–	dB
I_{tot}	total current consumption (DC)	note 3	–	395	410	mA

Notes

1. f_p = 55.25 MHz; V_p = 44 dBmV;
   f_q = 493.25 MHz; V_q = 44 dBmV;
   measured at $f_p + f_q$ = 548.5 MHz.
2. Measured according to DIN45004B;
   f_p = 540.25 MHz; $V_p = V_o$;
   f_q = 547.25 MHz; $V_q = V_o$ −6 dB;
   f_r = 549.25 MHz; $V_r = V_o$ − 6 dB;
   measured at $f_p + f_q - f_r$ = 538.25 MHz.
3. The module normally operates at V_B = 24 V, but is able to withstand supply transients up to 30 V.

PACKAGE OUTLINE

Rectangular single-ended package; aluminium flange; 2 vertical mounting holes; 2 x 6-32 UNC and 2 extra horizontal mounting holes; 7 gold-plated in-line leads **SOT115J**



DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A_2 max.	b	c	D max.	d	E max.	e	e_1	F	L min.	p	Q max.	q	q_1	q_2	S	U_1	U_2	W	w	x	y	Z max.
mm	20.8	9.5	0.51 0.38	0.25	27.2	2.04 2.54	13.75	2.54	5.08	12.7	8.8	4.15 3.85	2.4	38.1	25.4	10.2	4.2	44.75 44.25	8.2 7.8	6-32 UNC	0.25	0.7	0.1	3.8

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT115J						~~04-02-04~~ 10-06-18

DATA SHEET STATUS

DOCUMENT STATUS[1]	PRODUCT STATUS[2]	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

Contact information

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